



Product Overview

2N6341: 25 A, 150 V NPN Bipolar Power Transistor

For complete documentation, see the data sheet

Product Description

The Power 25A 150 V Bipolar NPN Transistor is designed for use in industrial-military power amplifier and switching circuit applications.

Features

- High Collector-Emitter Sustaining Voltage
 $V_{CEO(sus)} = 100 \text{ Vdc (Min)}$ 2N6338
 $V_{CEO(sus)} = 150 \text{ Vdc (Min)}$ - 2N6341
- High DC Current Gain
 $h_{FE} = 30 - 120 @ I_C = 10 \text{ Adc}$
 $h_{FE} = 12 \text{ (Min)} @ I_C = 25 \text{ Adc}$
- Low Collector-Emitter Saturation Voltage
 $V_{CE(sat)} = 1.0 \text{ Vdc (Max)} @ I_C = 10 \text{ Adc}$
- Fast Switching Times @ $I_C = 10 \text{ Adc}$
 $t_r = 0.3 \mu\text{s (Max)}$
 $t_s = 1.0 \mu\text{s (Max)}$
 $t_f = 0.25 \mu\text{s (Max)}$
- These devices are available in Pb-free package(s). Specifications herein apply to both standard and Pb-free devices. Please see our website at www.onsemi.com for specific Pb-free orderable part numbers, or contact your local ON Semiconductor sales office or representative.

Part Electrical Specifications

Product	Compliance	Status	Polarity	I_C Continuous (A)	$V_{(BR)CEO}$ Min (V)	h_{FE} Min	h_{FE} Max	f_T Min (MHz)	P_{TM} Max (W)	Package Type
2N6341G	Pb-free	Active	NPN	25	150	30	120	40	200	TO-204-2

For more information please contact your local sales support at www.onsemi.com

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